

General Purpose Transistors

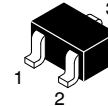
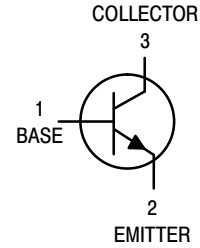
NPN Silicon

BC846, BC847, BC848

These transistors are designed for general purpose amplifier applications. They are housed in the SC-70/SOT-323 which is designed for low power surface mount applications.

Features

- S and NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant



SC-70/SOT-323
CASE 419
STYLE 3

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage BC846 BC847 BC848	V_{CEO}	65 45 30	V
Collector-Base Voltage BC846 BC847 BC848	V_{CBO}	80 50 30	V
Emitter-Base Voltage BC846 BC847 BC848	V_{EBO}	6.0 6.0 5.0	V
Collector Current – Continuous	I_C	100	mAdc

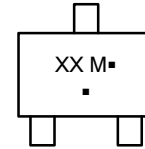
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board, (Note 1) $T_A = 25\text{ }^\circ\text{C}$	P_D	200	mW
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	620	$^\circ\text{C/W}$
Junction and Storage Temperature	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

1. FR-5 = 1.0 x 0.75 x 0.062 in.

MARKING DIAGRAM



XX = Specific Device Code
M = Month Code
■ = Pb-Free Package
(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering, marking and shipping information on page 12 of this data sheet.

BC846, BC847, BC848

ELECTRICAL CHARACTERISTICS ($T_A = 25\text{ }^\circ\text{C}$ unless otherwise noted)

Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Collector - Emitter Breakdown Voltage ($I_C = 10\text{ mA}$)	BC846 Series BC847 Series BC848 Series	$V_{(BR)CEO}$	65 45 30	- - -	- - -	V
Collector - Emitter Breakdown Voltage ($I_C = 10\text{ }\mu\text{A}$, $V_{EB} = 0$)	BC846 Series BC847 Series BC848 Series	$V_{(BR)CES}$	80 50 30	- - -	- - -	V
Collector - Base Breakdown Voltage ($I_C = 10\text{ }\mu\text{A}$)	BC846 Series BC847 Series BC848 Series	$V_{(BR)CBO}$	80 50 30	- - -	- - -	V
Emitter - Base Breakdown Voltage ($I_E = 1.0\text{ }\mu\text{A}$)	BC846 Series BC847 Series BC848 Series	$V_{(BR)EBO}$	6.0 6.0 5.0	- - -	- - -	V
Collector Cutoff Current ($V_{CB} = 30\text{ V}$) ($V_{CB} = 30\text{ V}$, $T_A = 150\text{ }^\circ\text{C}$)		I_{CBO}	- -	- -	15 5.0	nA μA

ON CHARACTERISTICS

DC Current Gain ($I_C = 10\text{ }\mu\text{A}$, $V_{CE} = 5.0\text{ V}$)	BC846A, BC847A, BC848A BC846B, BC847B, BC848B BC847C, BC848C	h_{FE}	- - -	90 150 270	- - -	-
($I_C = 2.0\text{ mA}$, $V_{CE} = 5.0\text{ V}$)	BC846A, BC847A, BC848A BC846B, BC847B, BC848B BC847C, BC848C		110 200 420	180 290 520	220 450 800	
Collector - Emitter Saturation Voltage ($I_C = 10\text{ mA}$, $I_B = 0.5\text{ mA}$) ($I_C = 100\text{ mA}$, $I_B = 5.0\text{ mA}$)		$V_{CE(sat)}$	- -	- -	0.25 0.6	V
Base - Emitter Saturation Voltage ($I_C = 10\text{ mA}$, $I_B = 0.5\text{ mA}$) ($I_C = 100\text{ mA}$, $I_B = 5.0\text{ mA}$)		$V_{BE(sat)}$	- -	0.7 0.9	- -	V
Base - Emitter Voltage ($I_C = 2.0\text{ mA}$, $V_{CE} = 5.0\text{ V}$) ($I_C = 10\text{ mA}$, $V_{CE} = 5.0\text{ V}$)		$V_{BE(on)}$	580 -	660 -	700 770	mV

SMALL-SIGNAL CHARACTERISTICS

Current - Gain - Bandwidth Product ($I_C = 10\text{ mA}$, $V_{CE} = 5.0\text{ Vdc}$, $f = 100\text{ MHz}$)		f_T	100	-	-	MHz
Output Capacitance ($V_{CB} = 10\text{ V}$, $f = 1.0\text{ MHz}$)		C_{obo}	-	-	4.5	pF
Noise Figure ($I_C = 0.2\text{ mA}$, $V_{CE} = 5.0\text{ Vdc}$, $R_S = 2.0\text{ k}\Omega$, $f = 1.0\text{ kHz}$, $BW = 200\text{ Hz}$)		NF	-	-	10	dB

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

BC846, BC847, BC848

BC846A, BC847A, BC848A

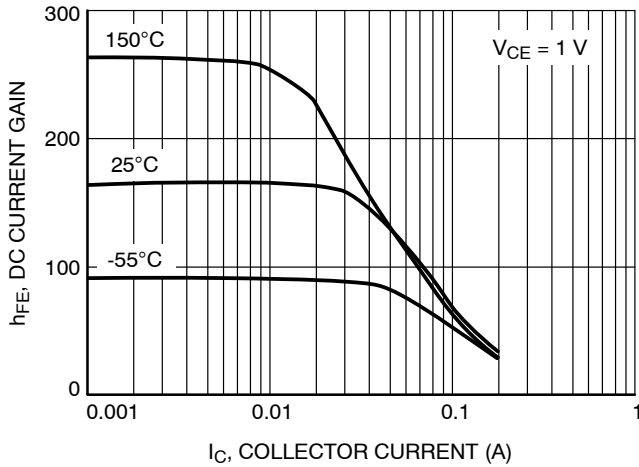


Figure 1. DC Current Gain vs. Collector Current

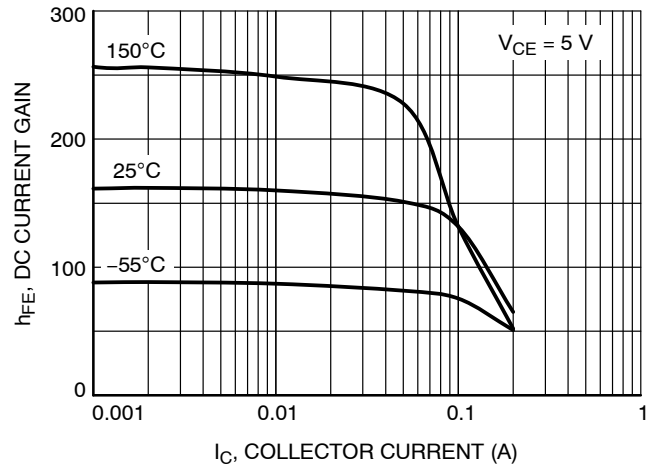


Figure 2. DC Current Gain vs. Collector Current

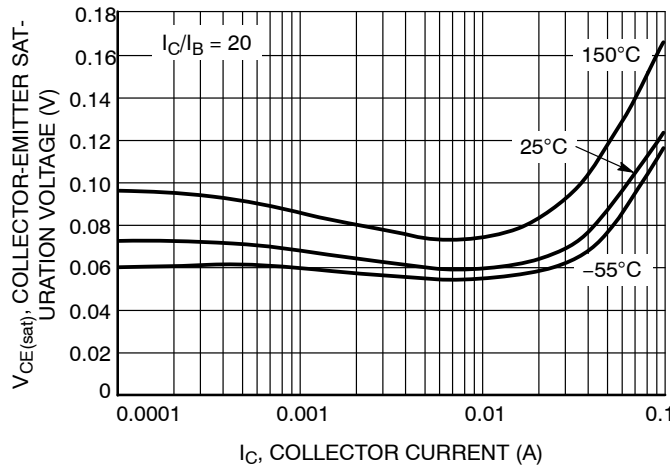


Figure 3. Collector-Emitter Saturation Voltage vs. Collector Current

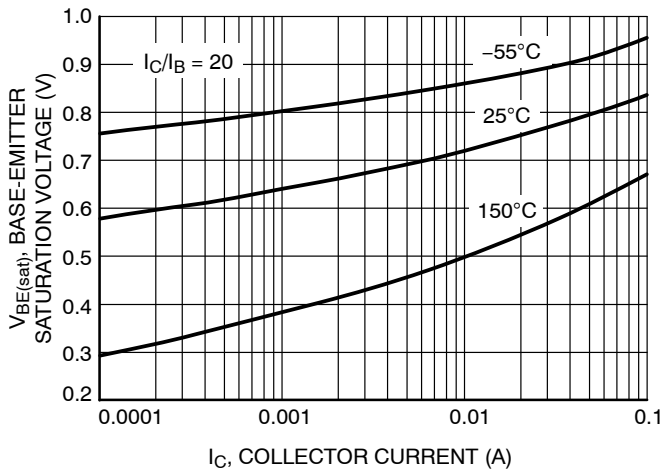


Figure 4. Base-Emitter Saturation Voltage vs. Collector Current

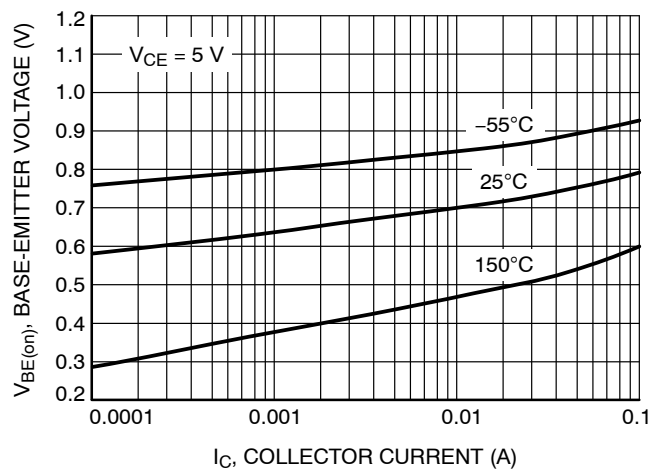


Figure 5. Base-Emitter Voltage vs. Collector Current

BC846, BC847, BC848

BC846A, BC847A, BC848A

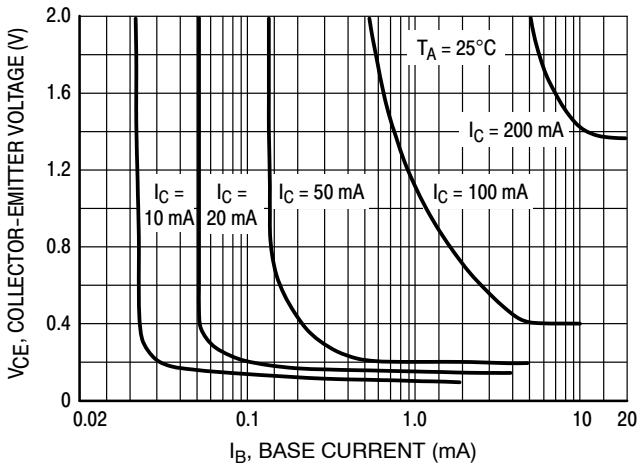


Figure 6. Collector Saturation Region

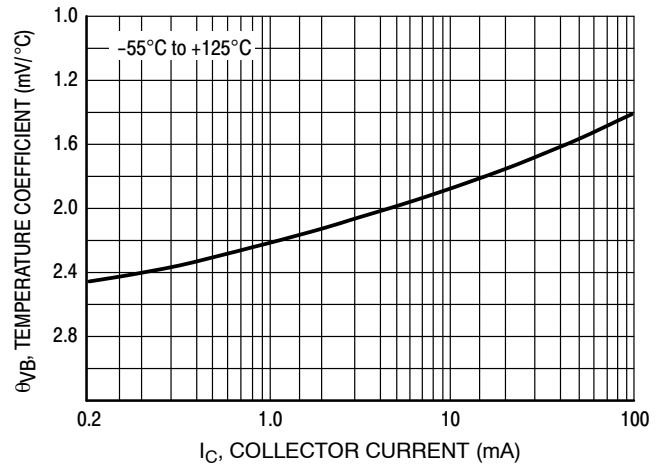


Figure 7. Base-Emitter Temperature Coefficient

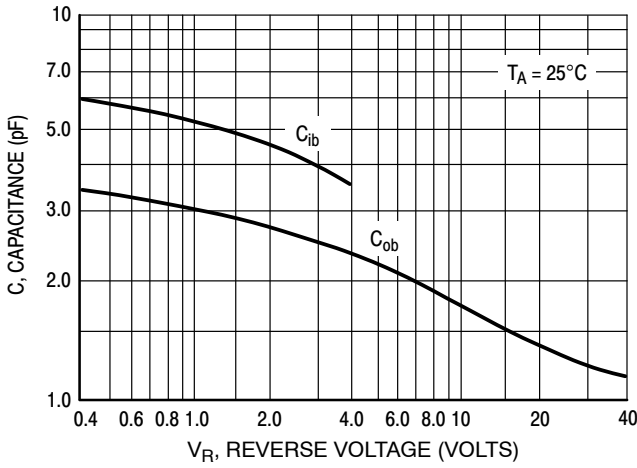


Figure 8. Capacitances

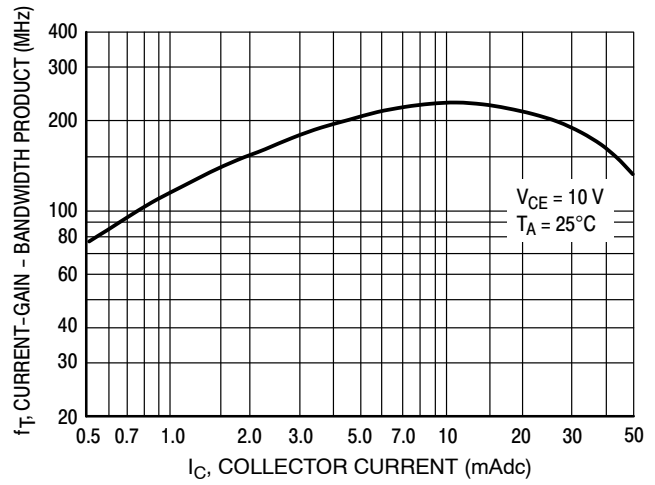


Figure 9. Current-Gain - Bandwidth Product

BC846B

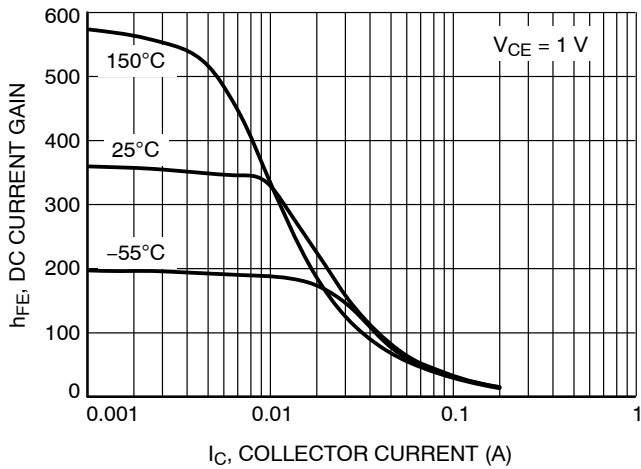


Figure 10. DC Current Gain vs. Collector Current

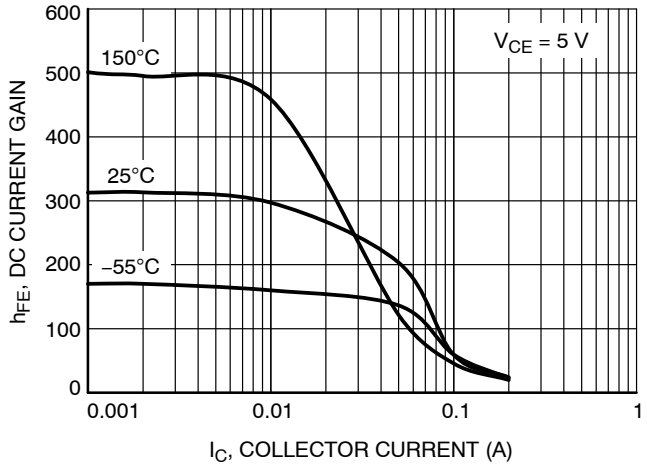


Figure 11. DC Current Gain vs. Collector Current

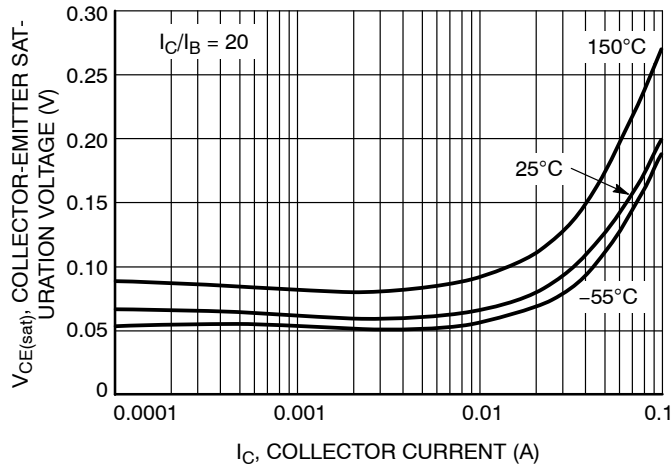


Figure 12. Collector Emitter Saturation Voltage vs. Collector Current

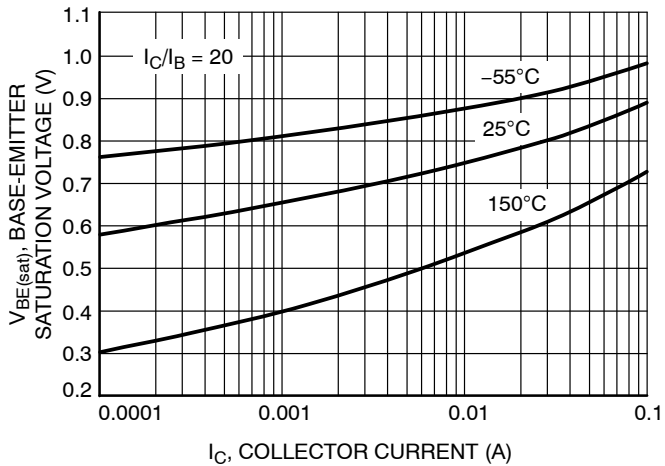


Figure 13. Base Emitter Saturation Voltage vs. Collector Current

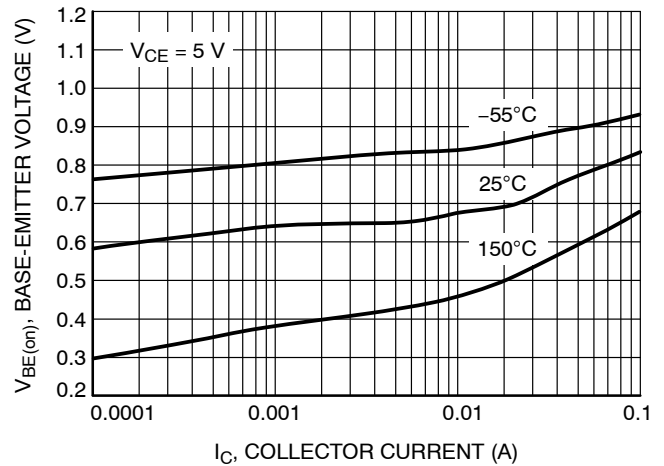


Figure 14. Base Emitter Voltage vs. Collector Current

BC846, BC847, BC848

BC846B

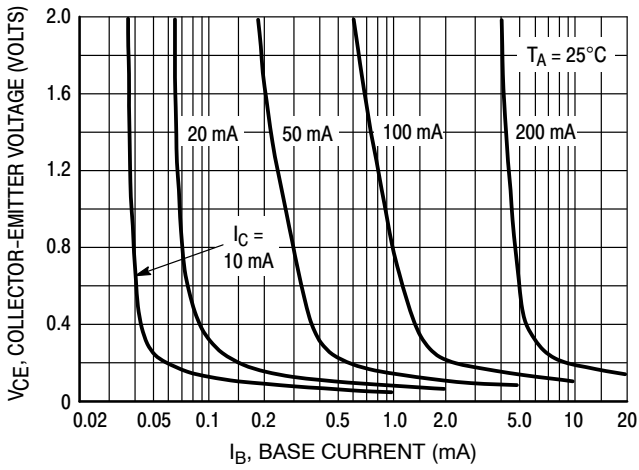


Figure 15. Collector Saturation Region

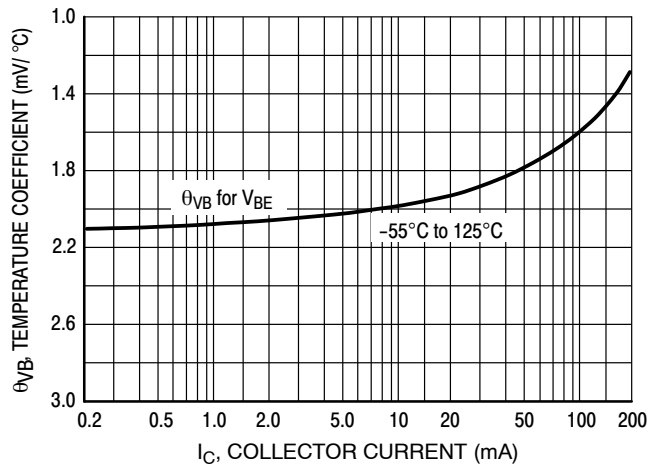


Figure 16. Base-Emitter Temperature Coefficient

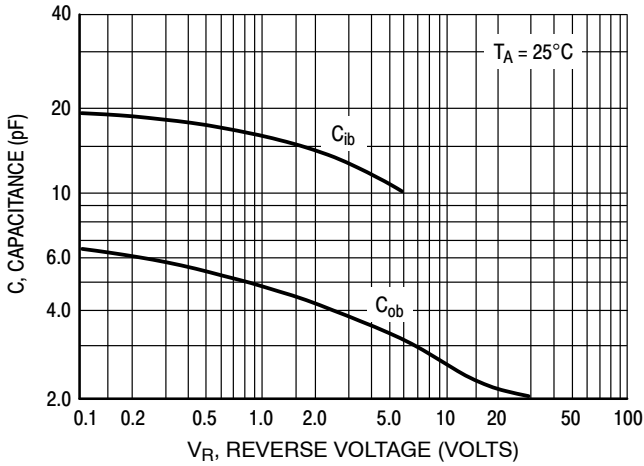


Figure 17. Capacitance

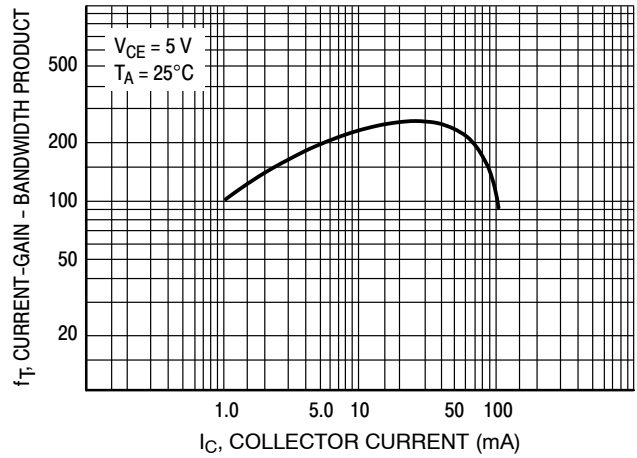


Figure 18. Current-Gain - Bandwidth Product

BC846, BC847, BC848

BC847B, BC848B

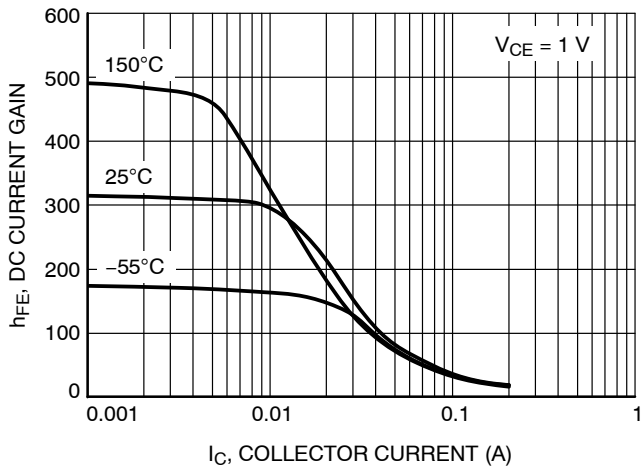


Figure 19. DC Current Gain vs. Collector Current

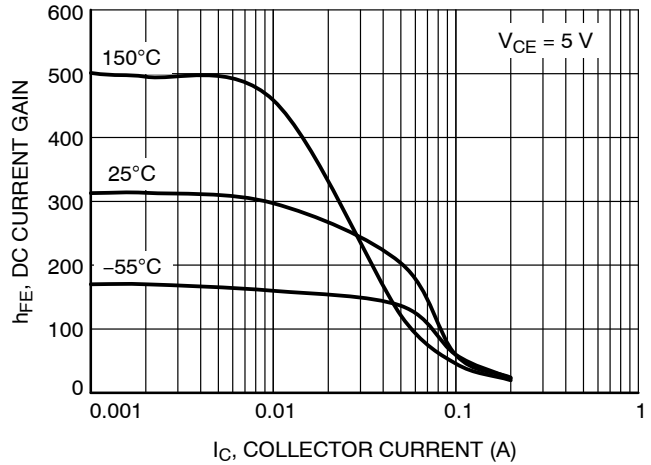


Figure 20. DC Current Gain vs. Collector Current

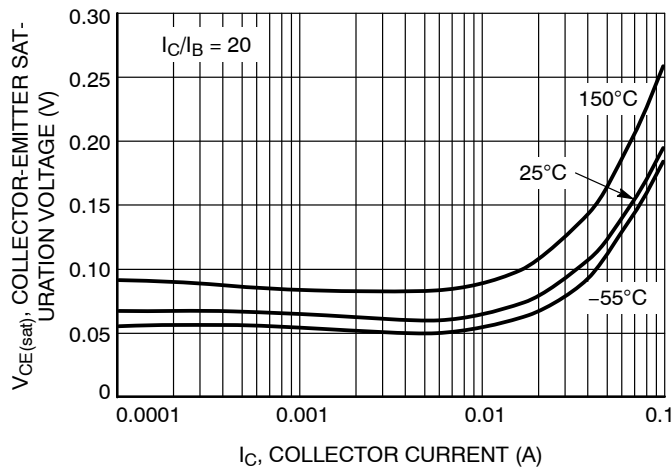


Figure 21. Collector-Emitter Saturation Voltage vs. Collector Current

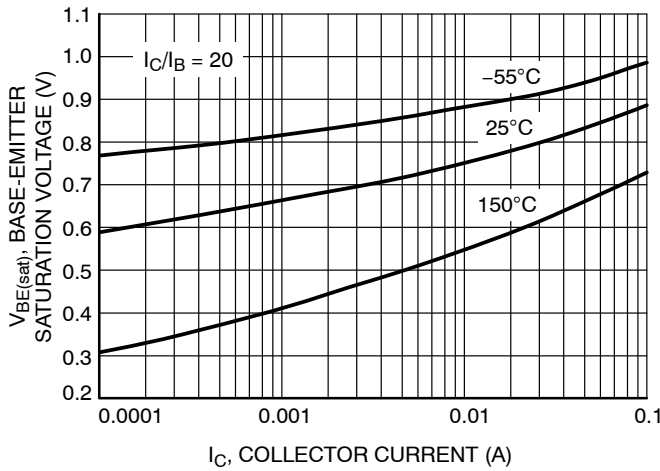


Figure 22. Base-Emitter Saturation Voltage vs. Collector Current

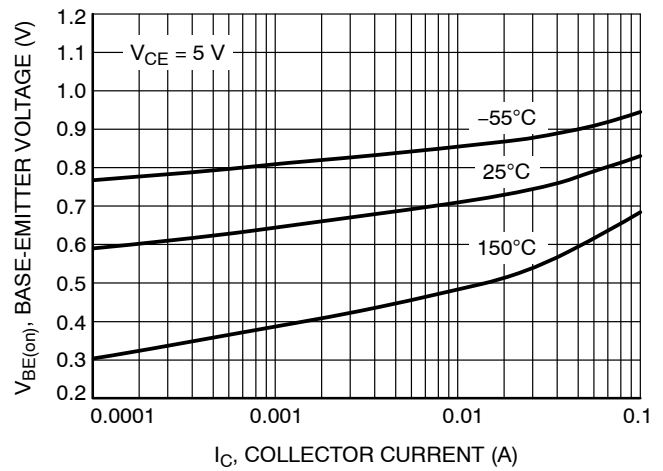


Figure 23. Base-Emitter Voltage vs. Collector Current

BC846, BC847, BC848

BC847B, BC848B

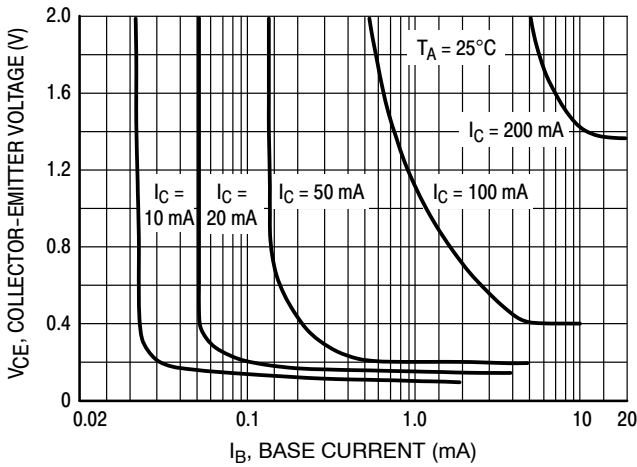


Figure 24. Collector Saturation Region

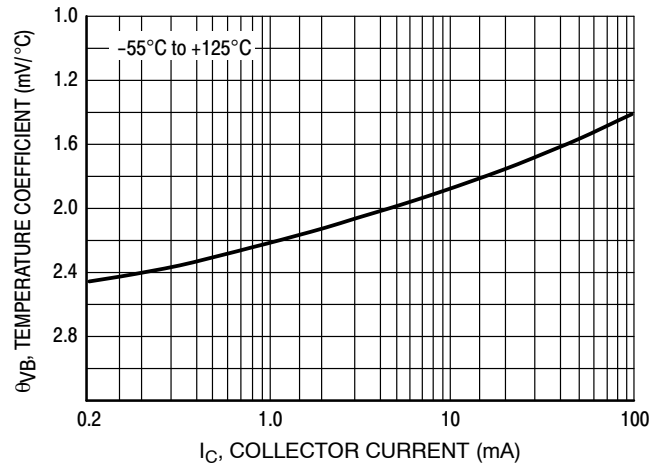


Figure 25. Base-Emitter Temperature Coefficient

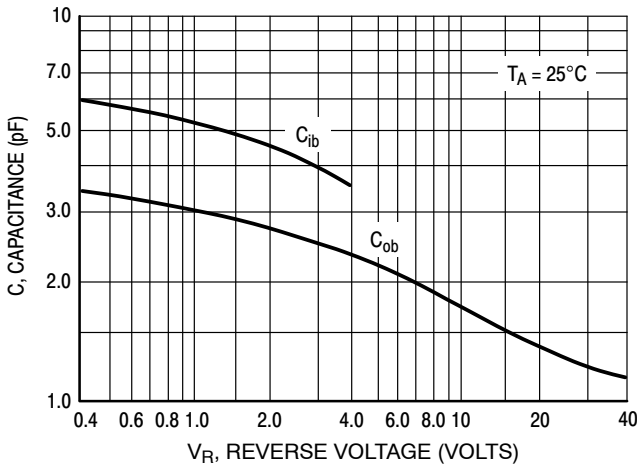


Figure 26. Capacitances

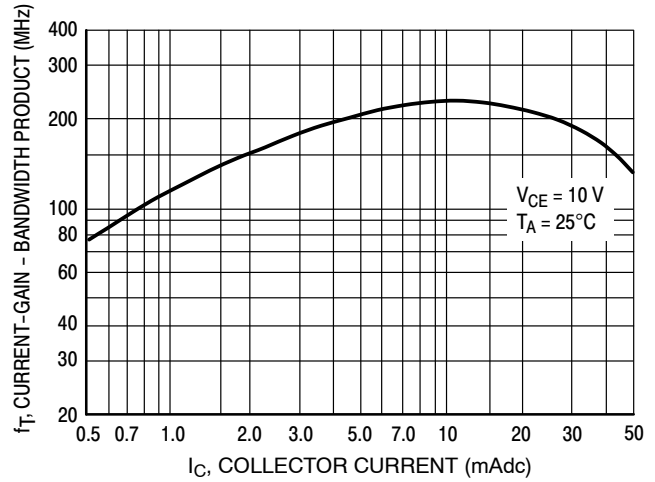


Figure 27. Current-Gain - Bandwidth Product

BC846, BC847, BC848

BC847C, BC848C

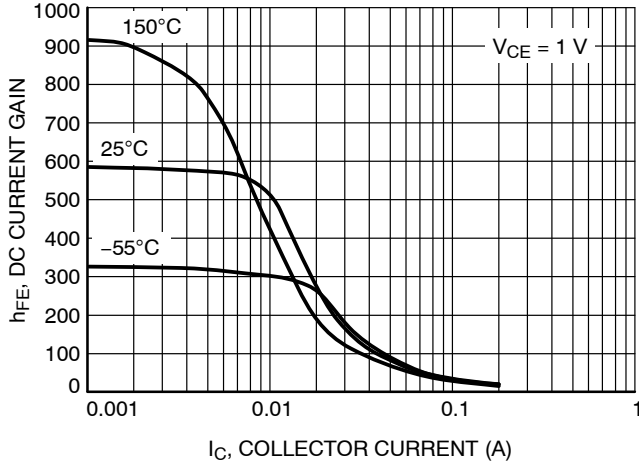


Figure 28. DC Current Gain vs. Collector Current

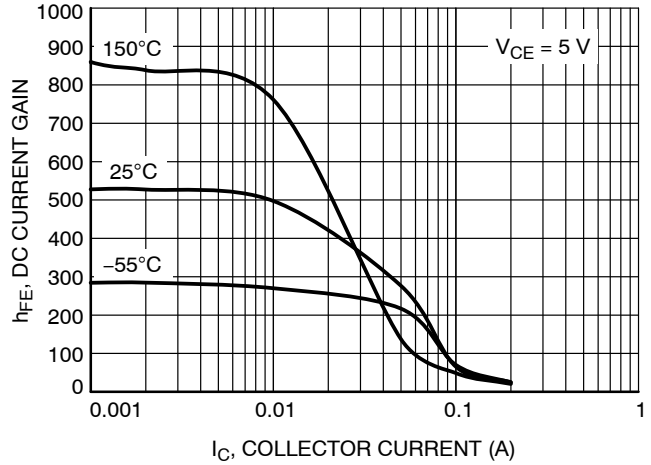


Figure 29. DC Current Gain vs. Collector Current

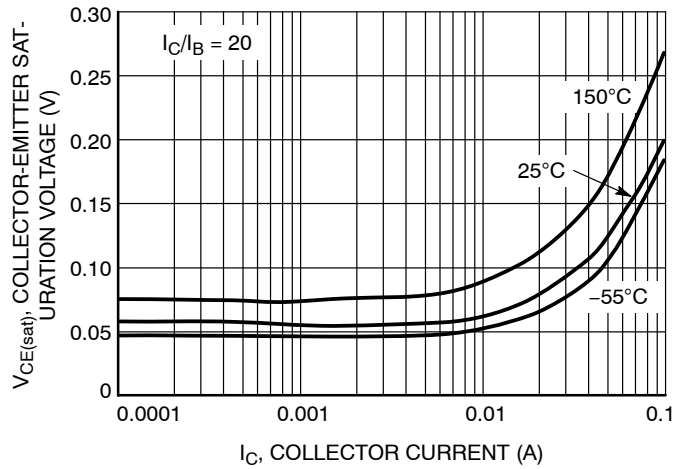


Figure 30. Collector Emitter Saturation Voltage vs. Collector Current

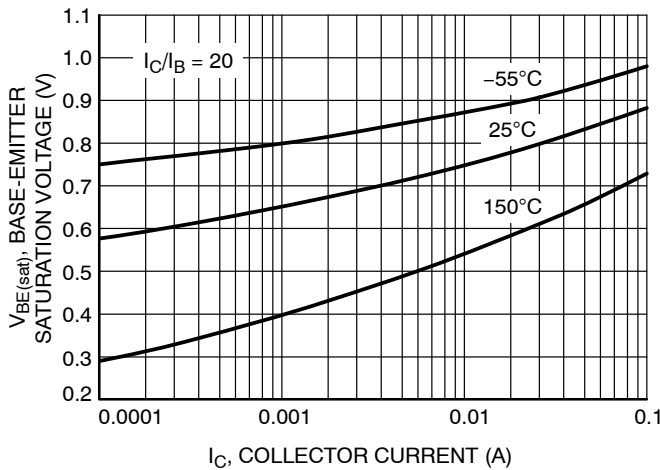


Figure 31. Base Emitter Saturation Voltage vs. Collector Current

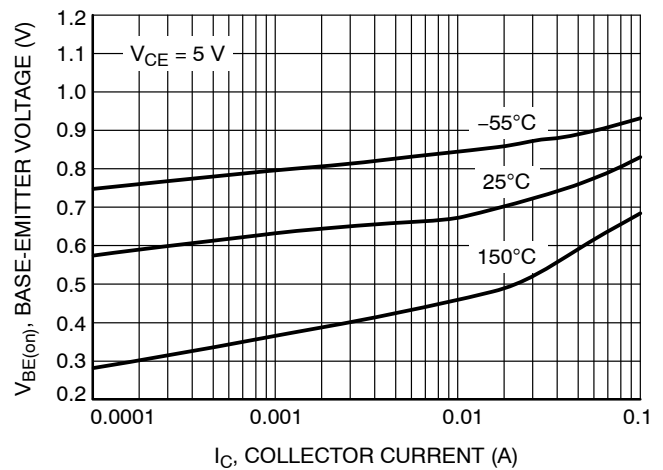


Figure 32. Base Emitter Voltage vs. Collector Current

BC846, BC847, BC848

BC847C, BC848C

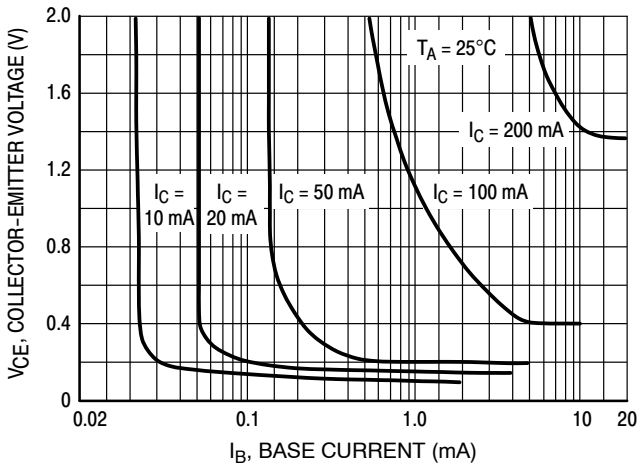


Figure 33. Collector Saturation Region

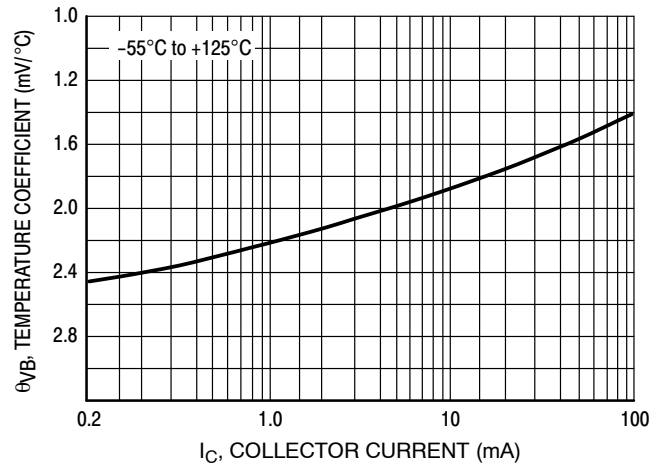


Figure 34. Base-Emitter Temperature Coefficient

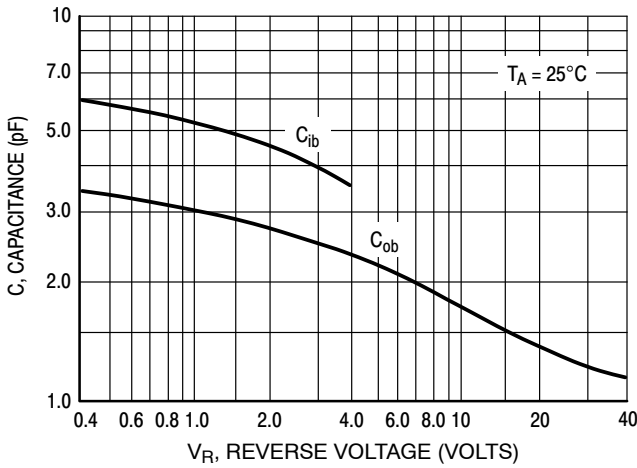


Figure 35. Capacitances

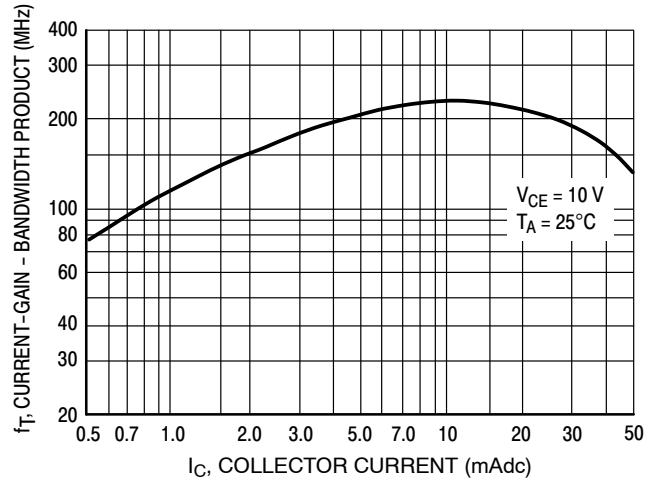


Figure 36. Current-Gain - Bandwidth Product

BC846, BC847, BC848

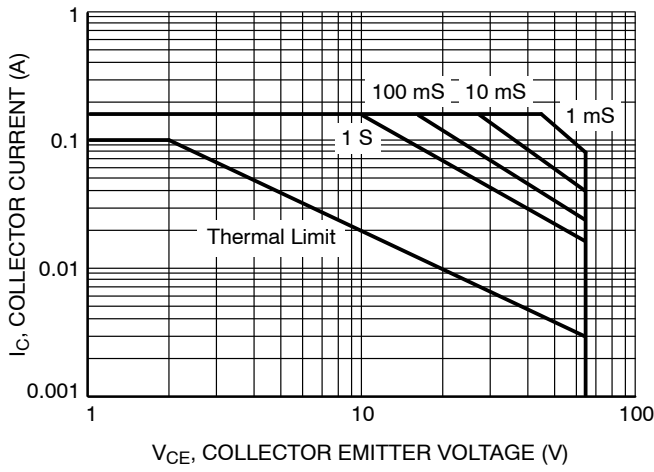


Figure 37. Safe Operating Area for BC846A, BC846B

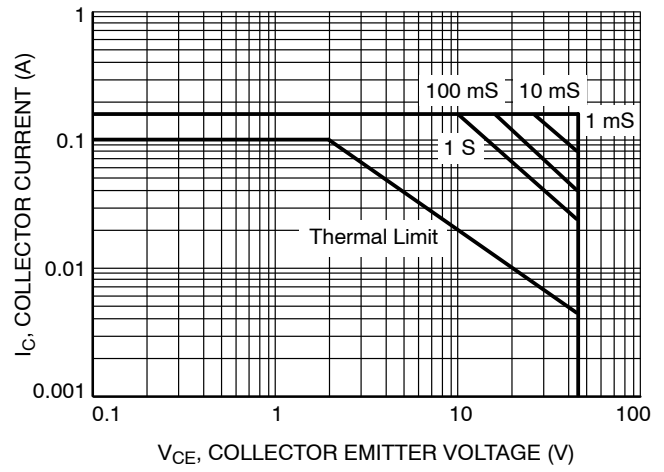


Figure 38. Safe Operating Area for BC847A, BC847B, BC847C

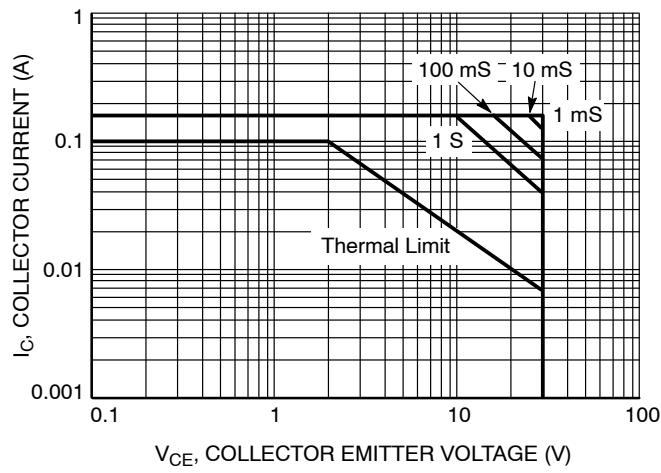


Figure 39. Safe Operating Area for BC848A, BC848B, BC848C

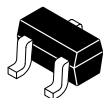
BC846, BC847, BC848

DEVICE ORDERING AND SPECIFIC MARKING INFORMATION

Device	Specific Marking Code	Package	Shipping†
BC846BWT1G	1B	SC-70 (SOT-323) (Pb-Free)	3,000 / Tape & Reel
SBC846BWT1G*			
BC847AWT1G	1E		3,000 / Tape & Reel
SBC847AWT1G*			
BC847BWT1G	1F		3,000 / Tape & Reel
SBC847BWT1G*			
BC847CWT1G	1G		3,000 / Tape & Reel
SBC847CWT1G*			
BC847CWT3G	1G		10,000 / Tape & Reel
SBC847CWT3G*			
BC848BWT1G	1K		3,000 / Tape & Reel
NSVBC848BWT1G*			
BC848CWT1G	1L		

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

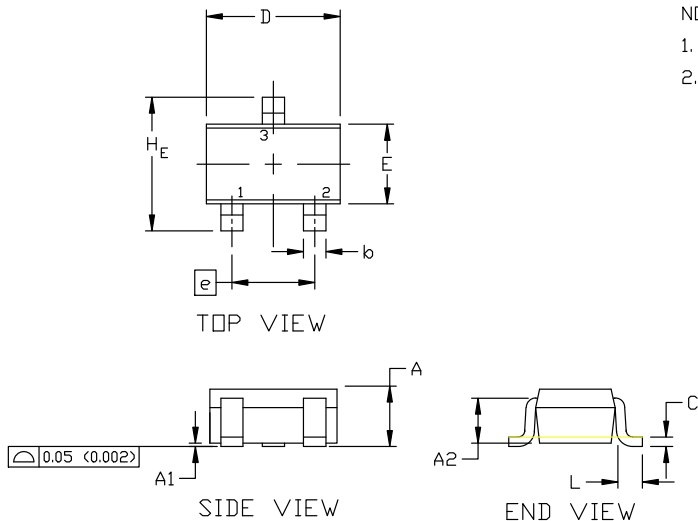
*S and NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.



SCALE 4:1

SC-70 (SOT-323)
CASE 419
ISSUE R

DATE 11 OCT 2022

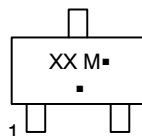


NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH

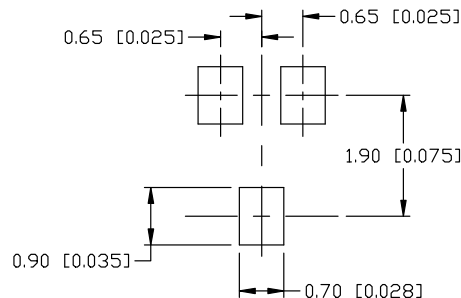
DIM	MILLIMETERS			INCHES		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	0.80	0.90	1.00	0.032	0.035	0.040
A1	0.00	0.05	0.10	0.000	0.002	0.004
A2	0.70 REF			0.028 BSC		
b	0.30	0.35	0.40	0.012	0.014	0.016
c	0.10	0.18	0.25	0.004	0.007	0.010
D	1.80	2.00	2.20	0.071	0.080	0.087
E	1.15	1.24	1.35	0.045	0.049	0.053
e	1.20	1.30	1.40	0.047	0.051	0.055
e1	0.65 BSC			0.026 BSC		
L	0.20	0.38	0.56	0.008	0.015	0.022
H _E	2.00	2.10	2.40	0.079	0.083	0.095

GENERIC
MARKING DIAGRAM



- XX = Specific Device Code
- M = Date Code
- = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.



* For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

SOLDERING FOOTPRINT

- | | | | | | |
|---|---|---|--|---|---|
| STYLE 1:
CANCELLED | STYLE 2:
PIN 1. ANODE
2. N.C.
3. CATHODE | STYLE 3:
PIN 1. BASE
2. EMITTER
3. COLLECTOR | STYLE 4:
PIN 1. CATHODE
2. CATHODE
3. ANODE | STYLE 5:
PIN 1. ANODE
2. ANODE
3. CATHODE | |
| STYLE 6:
PIN 1. EMITTER
2. BASE
3. COLLECTOR | STYLE 7:
PIN 1. BASE
2. EMITTER
3. COLLECTOR | STYLE 8:
PIN 1. GATE
2. SOURCE
3. DRAIN | STYLE 9:
PIN 1. ANODE
2. CATHODE
3. CATHODE-ANODE | STYLE 10:
PIN 1. CATHODE
2. ANODE
3. ANODE-CATHODE | STYLE 11:
PIN 1. CATHODE
2. CATHODE
3. CATHODE |

DOCUMENT NUMBER:	98ASB42819B	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
DESCRIPTION:	SC-70 (SOT-323)	PAGE 1 OF 1

onsemi and ONSEMI are trademarks of Semiconductor Components Industries, LLC dba onsemi or its subsidiaries in the United States and/or other countries. onsemi reserves the right to make changes without further notice to any products herein. onsemi makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does onsemi assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. onsemi does not convey any license under its patent rights nor the rights of others.

onsemi, **Onsemi**, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "**onsemi**" or its affiliates and/or subsidiaries in the United States and/or other countries. **onsemi** owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of **onsemi**'s product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. **onsemi** reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and **onsemi** makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using **onsemi** products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by **onsemi**. "Typical" parameters which may be provided in **onsemi** data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. **onsemi** does not convey any license under any of its intellectual property rights nor the rights of others. **onsemi** products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use **onsemi** products for any such unintended or unauthorized application, Buyer shall indemnify and hold **onsemi** and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that **onsemi** was negligent regarding the design or manufacture of the part. **onsemi** is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:

Technical Library: www.onsemi.com/design/resources/technical-documentation
onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support

For additional information, please contact your local Sales Representative at www.onsemi.com/support/sales